

CLAIM AMENDMENTS

1. (Currently Amended) A semiconductor device, comprising:
a conductive layer;
a first contact comprising a ball on said conductive layer;
a first bonding pad spaced apart from said conductive layer; and
a bonding wire electrically connecting said first contact to said first bonding pad and forming a second contact, said second contact including at least ~~two~~ first and second layers of said bonding wire, lying directly on each other, so that said bonding wire includes at least one reverse bend, and ~~one of the layers~~ said first layer is in contact with joined to both of said first bonding pad and said second layer and is between said second layer and said first bonding pad, directly opposite said first bonding pad.

2 and 3 (Cancelled)

4. (Previously Presented) The semiconductor device according to claim 1, wherein said conductive layer includes an inner lead.

5. (Currently Amended) The semiconductor device according to claim 1, comprising:
a base;
a semiconductor element on said base with a die pad interposed between said semiconductor element and said base;
a sealing resin sealing said semiconductor element; and
an external terminal on a rear surface of said base, wherein
said conductive layer includes a land on said base, and
said first bonding pad is on said semiconductor element.

6. (Previously Presented) The semiconductor device according to claim 1, comprising:
a base;
first and second semiconductor elements mounted on said base with a die pad interposed between said base and said first and second semiconductor elements;
a sealing resin sealing said first and second semiconductor elements; and
an external terminal on a rear surface of said base, wherein

said conductive layer includes a second bonding pad on said first semiconductor element, and
said first bonding pad is on said second semiconductor element.

7. (Previously Presented) A method of manufacturing a semiconductor device, comprising, sequentially:

joining a ball at a tip end of a bonding wire to a conductive layer as a first contact;

joining a first part of said bonding wire directly to a bonding pad;

mechanically deforming a second part of said bonding wire, while said first part of said bonding wire is joined to said bonding pad, so that said second part of said bonding wire, is folded onto said first part of said bonding wire, directly opposite said bonding pad with said first part of said bonding wire between said bonding pad and said second part of said bonding wire; and

joining said second part of said bonding wire to said first part of said bonding wire while said first part of said bonding wire is on said bonding pad.

8 and 9 (Cancelled)

10. (Previously Presented) The method of manufacturing a semiconductor device according to claim 7, wherein

said bonding wire is held by a bonding tool; and

mechanically deforming said bonding wire includes mechanically deforming said bonding wire on said bonding pad by moving said bonding tool with said bonding wire joined to said bonding pad.